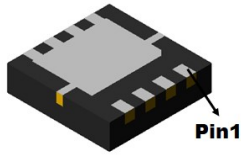
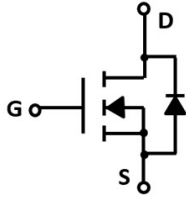
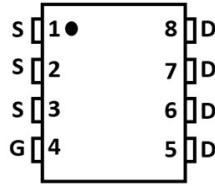


N-Channel Enhancement Mode Field Effect Transistor



DFN3.3X3.3



Product Summary

- V_{DS} 30V
- I_D 30A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) < 9 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) < 13 mohm
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- High current load applications
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	30	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_C=25^\circ\text{C}$	30
		$T_C=100^\circ\text{C}$	21
Pulsed Drain Current ^A	I_{DM}	115	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	21
		$T_C=100^\circ\text{C}$	10.5
Single Pulse Avalanche Energy ^B	E_{AS}	112	mJ
Thermal Resistance Junction-to-Case ^C	$R_{\theta JC}$	7.1	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+175	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ30N03A	F1	Q30N03	5000	10000	100000	13" reel



YJQ30N03A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	T _J =25°C		1	μA
			T _J =55°C		5	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	R _{D(S)ON}	V _{GS} = 10V, I _D =15A		5.8	9	mΩ
		V _{GS} = 4.5V, I _D =15A		10	13	
Diode Forward Voltage	V _{SD}	I _S =15A, V _{GS} =0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I _S				30	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHZ		1015		pF
Output Capacitance	C _{oss}			201		
Reverse Transfer Capacitance	C _{rss}			164		
Gate Resistance	R _g	f= 1MHZ		1.5	3	Ω
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =20A		23.6		nC
Total Gate Charge	Q _{g(4.5V)}			12.9		
Gate-Source Charge	Q _{gs}			3.9		
Gate-Drain Charge	Q _{gd}			7		
Reverse Recovery Charge	Q _{rr}	I _F =15A, di/dt=100A/us		0.2		ns
Reverse Recovery Time	t _{rr}			5		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =20V, I _D =2A, R _{GEN} =3Ω		7		ns
Turn-on Rise Time	t _r			19		
Turn-off Delay Time	t _{D(off)}			24		
Turn-off fall Time	t _f			24		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

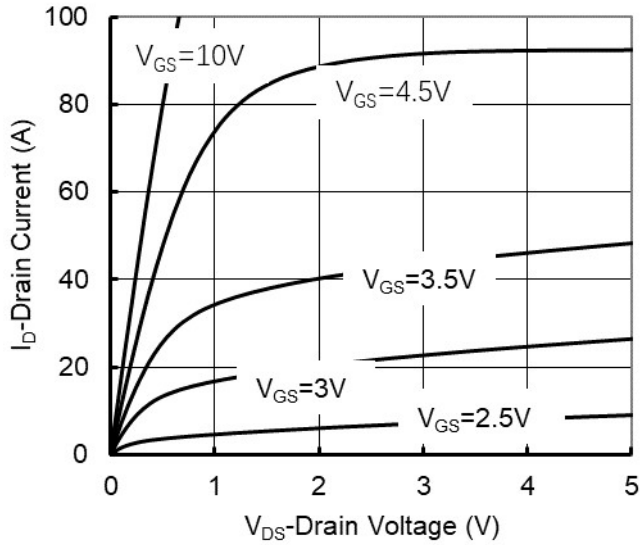


Figure1. Output Characteristics

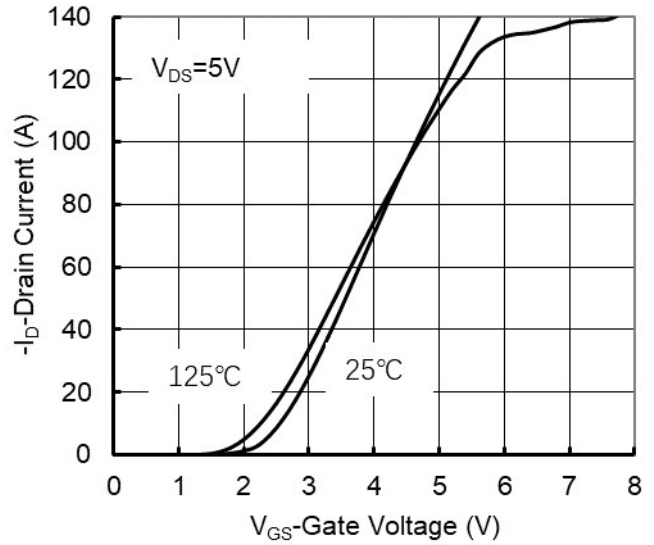


Figure2. Transfer Characteristics

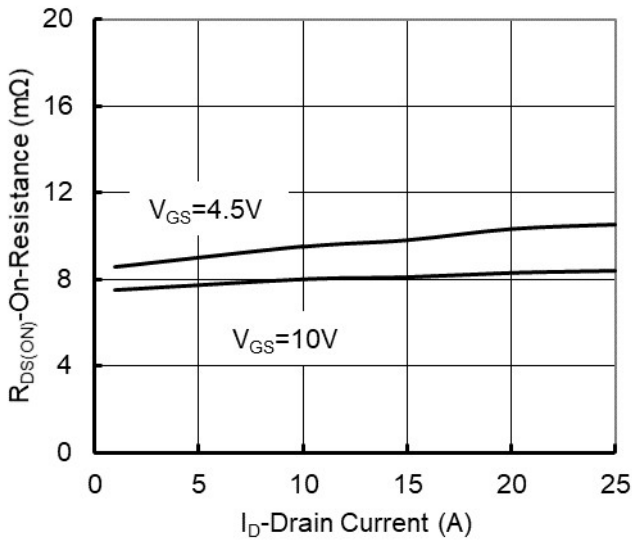


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

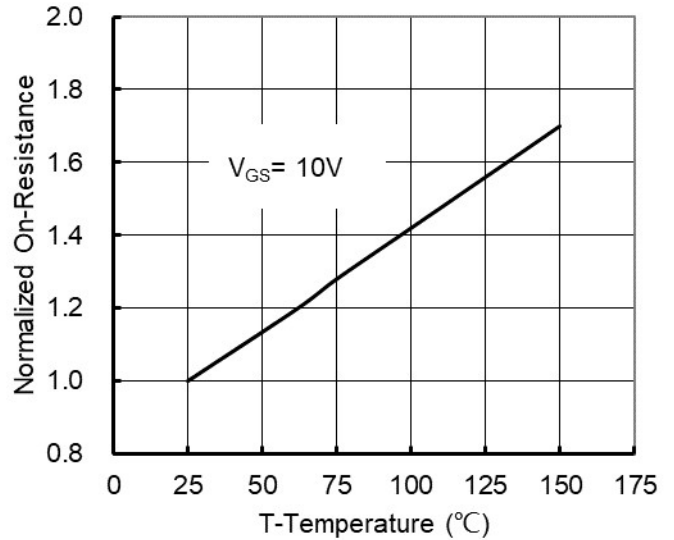


Figure 4: On-Resistance vs. Junction Temperature

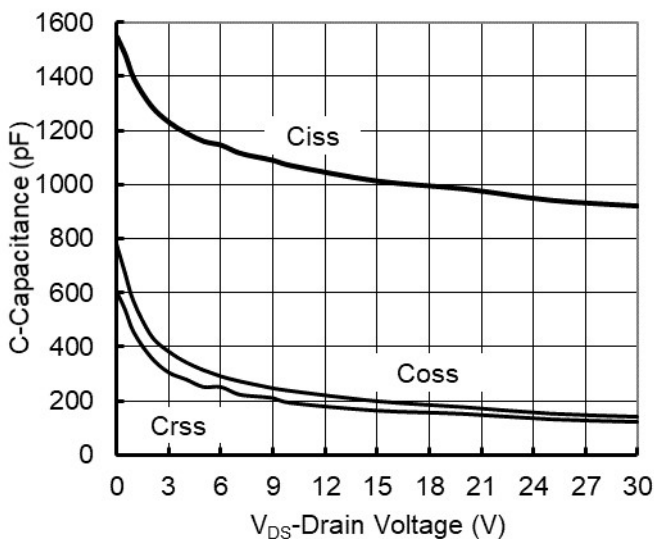


Figure5. Capacitance Characteristics

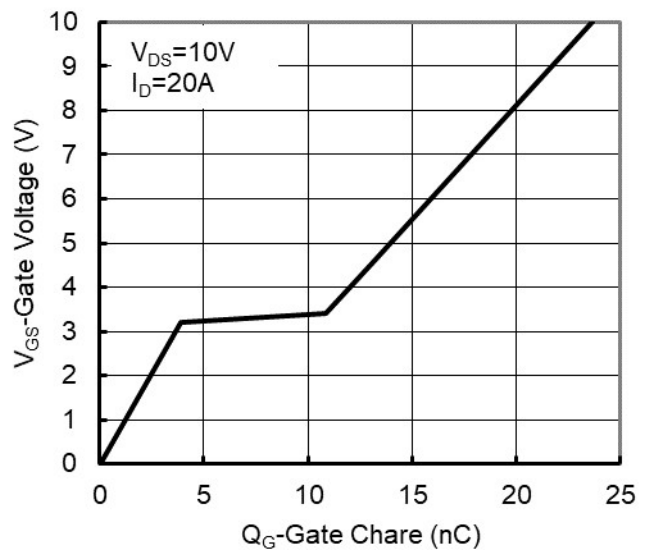


Figure6. Gate Charge



YJQ30N03A

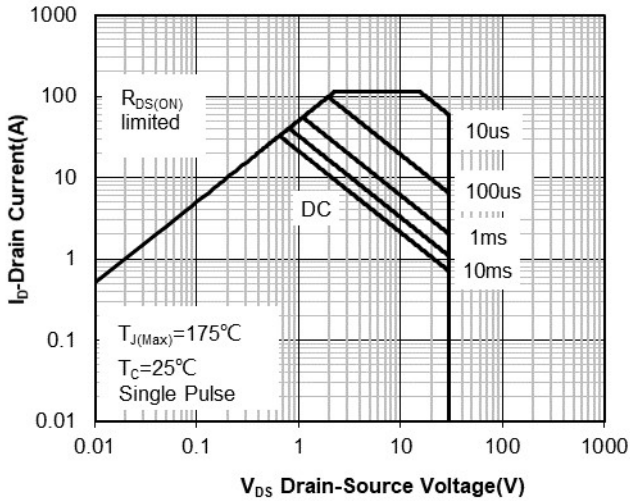


Figure7. Safe Operation Area

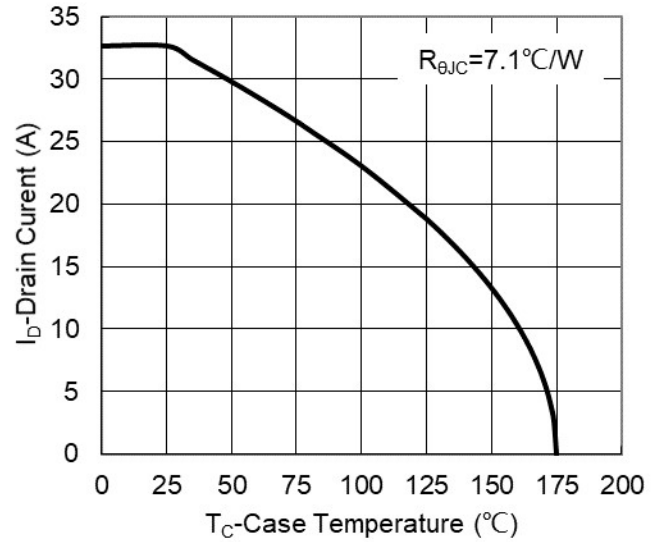


Figure8. Maximum Continuous Drain Current vs Case Temperature

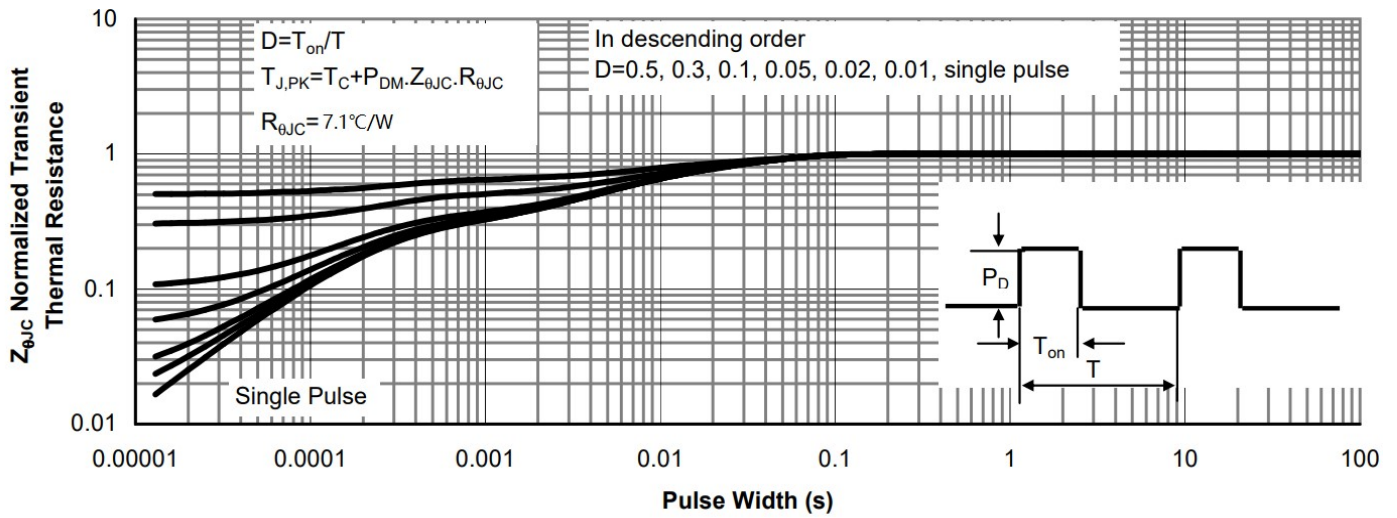


Figure9. Normalized Maximum Transient Thermal Impedance



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

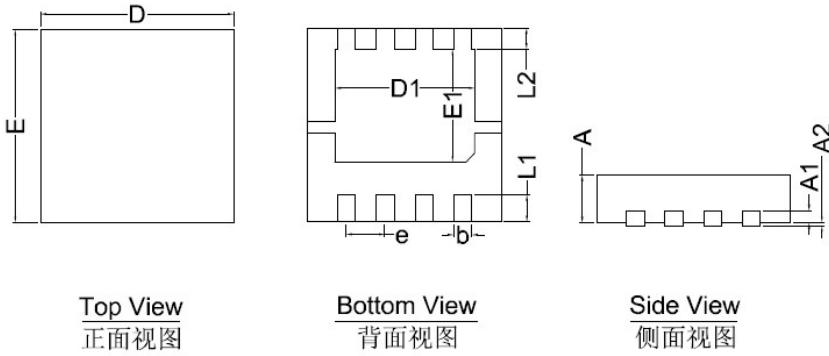


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

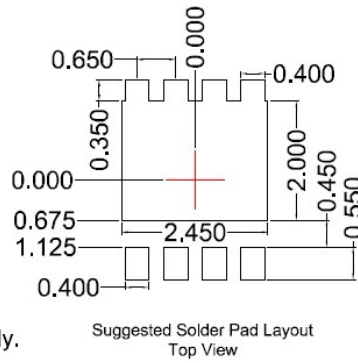


YJQ30N03A

■DFN3.3X3.3 Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	3.15	3.25	3.35
E	3.15	3.25	3.35
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	2.20	2.35	2.50
E1	1.80	1.90	2.00
L1	0.35	0.45	0.55
L2	0.35 BSC		
b	0.20	0.30	0.40
e	0.65 BSC		



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.10\text{mm}$.
 3. The pad layout is for reference purposes only.



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